Anomalous Hall Effect and Perpendicular Magnetic Anisotropy in Ultrathin Ferrimagnetic NiCo$_2$O$_4$ Films

Xuegang Chen,$^{1,2,*}$ Qiuchen Wu,$^{1,*}$ Le Zhang,$^1$ Yifei Hao,$^1$ Myung-Geun Han,$^3$ Yimei Zhu,$^3$ Xia Hong$^{1,a}$

$^1$ Department of Physics and Astronomy & Nebraska Center for Materials and Nanoscience, University of Nebraska–Lincoln, Lincoln, NE 68588-0299, USA

$^2$ Institutes of Physical Science and Information Technology, Anhui University, Hefei 230601, People’s Republic of China

$^3$ Condensed Matter Physics and Materials Science Department, Brookhaven National Laboratory, Upton, NY 11973-5000, USA

* These authors contributed equally

a) Author to whom correspondence should be addressed: xia.hong@unl.edu

Abstract

The inverse spinel ferrimagnetic NiCo$_2$O$_4$ possesses high magnetic Curie temperature $T_C$, high spin polarization, and strain-tunable magnetic anisotropy. Understanding the thickness scaling limit of these intriguing magnetic properties in NiCo$_2$O$_4$ thin films is critical for their implementation in nanoscale spintronic applications. In this work, we report the unconventional magnetotransport properties of epitaxial (001) NiCo$_2$O$_4$ films on MgAl$_2$O$_4$ substrates in the ultrathin limit. Anomalous Hall effect measurements reveal strong perpendicular magnetic anisotropy for films down to 1.5 unit cell (1.2 nm), while $T_C$ for 3 unit cell and thicker films remains above 300 K. The sign change in the anomalous Hall conductivity ($\sigma_{xy}$) and its scaling
relation with the longitudinal conductivity ($\sigma_{xx}$) can be attributed to the competing effects between impurity scattering and band intrinsic Berry curvature, with the latter vanishing upon the thickness driven metal-insulator transition. Our study reveals the critical role of film thickness in tuning the relative strength of charge correlation, Berry phase effect, spin orbit interaction, and impurity scattering, providing important material information for designing scalable epitaxial magnetic tunnel junctions and sensing devices using NiCo$_2$O$_4$.

Magnetic thin films with high spin polarization, high Curie temperature, and perpendicular magnetic anisotropy (PMA) are important material solutions for transcending the fundamental limits of operation speed and energy efficiency in spintronics.\textsuperscript{1, 2} A promising material candidate is the ferrimagnetic inverse spinel NiCo$_2$O$_4$ (NCO), which possesses majority spins associated with the tetrahedral ($T_d$) site Co ions and the minority spins originating from the octahedral ($O_h$) site Ni ions [Fig. 1(a)]. Previous studies have shown that epitaxial NCO films exhibit intriguing magnetotransport properties,\textsuperscript{3-5} strain tunable magnetic anisotropy,\textsuperscript{6} and spin polarization as high as -73%.\textsuperscript{7} Being lattice matched with the high performance tunnel barrier candidate, MgAl$_2$O$_4$, it can be utilized as the spin injection layer for epitaxial magnetic tunnel junctions (MTJ),\textsuperscript{7-10} which can potentially suppress the band-folding effect and lead to enhanced tunneling magnetoresistance.\textsuperscript{11} Compared with devices based on amorphous tunnel barrier and electrode layers, MTJs based on epitaxial NCO/MgAl$_2$O$_4$/NCO heterostructures also facilitate the understanding of symmetry-based spin filtering effect.\textsuperscript{12} Despite the emerging interests in epitaxial NCO thin films,\textsuperscript{2-7, 13-18} fundamental understanding of the thickness scaling behavior of its intriguing magnetic properties remains elusive.
In this work, we report the observation of unconventional anomalous Hall effect (AHE) and strong PMA in ultrathin (001) NCO films strained on MgAl$_2$O$_4$ substrates. The Curie temperature ($T_C$) of the NCO films remains above 300 K in films as thin as 3 unit cell (uc), while PMA is sustained even in 1.5 uc films. The anomalous Hall resistance shows a temperature-driven sign change, evolving from clockwise hysteresis at high temperature to counterclockwise hysteresis at low temperature. The scaling behavior between anomalous Hall conductivity ($\sigma_{xy}$) and longitudinal conductivity ($\sigma_{xx}$) point to the collective contributions of spin-dependent scattering in the dirty metal regime and band intrinsic Berry phase effect to the AHE in the metallic phase, with the latter vanishing upon the thickness driven metal-insulator transition.

We deposited epitaxial NCO films on (001) MgAl$_2$O$_4$ substrates via off-axis radio frequency magnetron sputtering at 320 °C in 100 mTorr processing gas (Ar:O$_2$ = 1:1). X-ray diffraction (XRD) measurement reveals (001)-oriented growth with no impurity phase [Fig. 1(b)]. The $\theta$-2$\theta$ spectrum shows clear Laue oscillations around the (001) peak, which was used to calibrate the growth rate. The c-axis lattice constant is 8.20 Å, higher than the bulk cubic lattice parameter (8.13 Å), which is consistent with a strained film on MgAl$_2$O$_4$ ($a = 8.08$ Å). The high crystallinity of the samples is clearly revealed by the high-angle annular dark-field scanning transmission electron microscopy (HAADF-STEM) and selected area electron diffraction (SAED) [Fig. 1(c)]. The as-grown NCO films show smooth surface morphology with a typical surface roughness of 2-3 Å [Fig. 1(d)]. We fabricated the samples into van der Pauw device geometry for magnetotransport studies. The measurements were carried out in a Quantum Design Physical Property Measurement System using Keithley 2400 SourceMeter or standard lock-in technique (SR830) with low excitation current ($\leq$10 µA). We studied two samples for each thickness and the results are highly consistent.
Figure 1(e) shows the temperature dependence of the longitudinal sheet resistance $R_\parallel$ of 1.5-5 uc NCO films. For the 3-5 uc samples, $R_\parallel$ shows a moderate, metallic $T$-dependence ($dR/dT > 0$) below 350 K, consistent with those reported for thick NCO films.\textsuperscript{3, 13, 14} A resistance upturn appears ($dR/dT < 0$) in the low temperature regime, and the upturn temperature ($T_{up}$) increases gradually with reducing film thickness. The moderate $T$-dependence of $R_\parallel$ below $T_{up}$ is the signature behavior of weakly localized conductors, which can be due to quantum interference effect associated with electron back-scattering or enhanced electron-electron interaction.\textsuperscript{19} The 1.5 uc film becomes insulating over the entire temperature range, with $R_\parallel(T)$ well described by variable range hoping. The transition to the strongly localized behavior occurs in the 2 uc film as $R_\parallel$ approaches $\frac{h}{e^2} \sim 25.9$ kΩ. This thickness-driven metal-insulator transition has been widely observed in correlated oxide thin films, which may originate from a dimensionality crossover,\textsuperscript{19, 20} energy gap formation due to enhanced electron-electron correlation in the ultrathin films,\textsuperscript{19, 21} and variation in oxygen octahedral distortion\textsuperscript{22} or enhanced impurity/defect states\textsuperscript{17} at surfaces/interfaces.

Figure 2(a) shows the AHE hysteresis taken in the NCO films at 100 K. The Hall resistivity is calculated using $\rho_{xy} = R_{xy}t_{NCO}$, with $R_{xy}$ the Hall resistance and $t_{NCO}$ the film thickness. It can be decomposed into the normal Hall and AHE contributions:

$$\rho_{xy} = R_0 H + \rho_{AHE}. \quad (1)$$

Here $R_0 = 1/en_{eff}$ is the normal Hall coefficient with $n_{eff}$ the effective carrier density, $H$ is the out-of-plane magnetic field, and $\rho_{AHE}$ is the anomalous Hall resistivity. All samples exhibit counterclockwise AHE hysteresis, which is defined as positive for $\rho_{AHE}$. The coercive field ($H_c$) is significantly reduced in the 1.5 and 2 uc films [Fig. 2(b)], which may be attributed to domain
nucleation and domain wall motion promoted by interfacial defects\textsuperscript{23} and/or enhanced thermal fluctuation with reduced dimension. The sharp switching of the AHE hysteresis suggests that the PMA is preserved in NCO films as thin as 1.5 uc. This can be well accounted for by the 0.6\% compressive strain for (001) NCO deposited on MgAl\textsubscript{2}O\textsubscript{4}, which yields meV level magnetic anisotropic energy between the in-plane and out-of-plane orientations, well exceeding the shape anisotropy.\textsuperscript{3, 6, 14} We identified $T_C$ for the NCO films from the temperature dependence of $\rho_{\text{AHE}}$. As shown in Fig. 2(c), $T_C$ is above 300 K for the 3-5 uc NCO films and decreases to 230 K for the 2 uc (1.6 nm) NCO and 170 K for the 1.5 uc (1.2 nm) film. Figure 2(d) shows the $T_C$ at the ultrathin limit for various widely studied magnetic nanomaterials, including epitaxial thin films of correlated oxides SrRuO\textsubscript{3} (SRO)\textsuperscript{24} and La\textsubscript{0.7}Sr\textsubscript{0.3}MnO\textsubscript{3} (LSMO)\textsuperscript{25} and two-dimensional (2D) van der Waals (vdW) magnets, such as VSe\textsubscript{2},\textsuperscript{26} MnSe\textsubscript{2},\textsuperscript{27} CrSe\textsubscript{2},\textsuperscript{28} CrI\textsubscript{3},\textsuperscript{29} CrCl\textsubscript{3},\textsuperscript{30} Fe\textsubscript{3}GeTe\textsubscript{2} (FGT),\textsuperscript{31, 32} and Cr\textsubscript{2}Ge\textsubscript{2}Te\textsubscript{6} (CGT).\textsuperscript{33} The combined high $T_C$ and strong PMA of ultrathin NCO films outperform most magnetic oxides. Compared to 2D vdW magnets, it offers not only highly competitive material parameters but also the distinct advantage of highly scalable growth. High quality epitaxial ultrathin films can be achieved at large scale and the film thickness can be controlled with atomic precision. These features make NCO a highly promising material candidate for developing nanoscale magnetic applications.

One interesting property of NCO is the AHE exhibits a nonmonotonic temperature dependence that leads to temperature/film thickness driven sign change in $\rho_{\text{AHE}}$\textsuperscript{3} Figure 3(a) shows $R_{xy}$ measured on the 2 uc (1.6 nm) film at various temperatures. Above $T_C$ of 230 K, $R_{xy}$ exhibits a linear $H$-dependence, corresponding to the normal Hall effect. A clear nonlinear $H$-dependence appears below $T_C$, signaling the appearance of AHE. The magnitude of anomalous Hall resistance $R_{\text{AHE}} = \rho_{\text{AHE}}/t_{\text{NCO}}$ first increases below $T_C$, which can be attributed to the rapid increase of $M$. 
After reaching a local maximum value at 190 K, $R_{\text{AHE}}$ starts to decrease with decreasing temperature, and crosses zero at $T_{sc} = 150$ K. Similar $T$-dependence of $R_{\text{AHE}}$ has been observed in all ultrathin films [Fig. 3(b)]. As shown in Fig. 3(c), the transition from a negative hysteresis (clockwise) to a positive hysteresis (counterclockwise) occurs smoothly without any abrupt jump in $R_{\text{AHE}}$. The sign change temperature $T_{sc}$ ranges from 110 K to 150 K and does not exhibit an apparent dependence on film thickness [Fig. 2(c)]. As NCO is a multiband conductor,\textsuperscript{15} we also examined the effective carrier type. Figure 3(d) shows the effective carrier density of the 2 uc sample calculated from the high field (up to 50 kOe) normal Hall effect ($n_{\text{eff}} = 1/eR_0$). The charge carrier type evolves from electron-like ($R_0 < 0$) to hole-like ($R_0 > 0$) as the sample is cooled below 200 K. This transition temperature is much higher than $T_{sc}$, confirming that the sign change of $R_{\text{AHE}}$ is not due to the change of carrier type. The corresponding $H_c$ increases exponentially with decreasing temperature [Fig. 3(e)], pointing to thermally activated domain wall depinning.\textsuperscript{23} The smooth $T$-dependences of $R_{\text{AHE}}$ and $H_c$ [Fig. 3(f)] also indicate that the sign change in AHE is not induced by an abrupt change of magnetic state in the samples.

Previous studies of thick NCO films show that multiple mechanisms can contribute to the observed anomalous Hall resistance, whose competition can lead to the sign change phenomenon.\textsuperscript{3} Based on quantum transport theory of multiband magnetic conductors, the scaling relation between the AHE conductivity $\sigma_{xy} = \rho_{xy}/\rho_{xx}^2$ and longitudinal conductivity $\sigma_{xx}$ depends on the relative strength of impurity scattering rate with respect to the Fermi energy:\textsuperscript{34}

\begin{align}
\sigma_{xy} &= \text{constant} \quad (\text{moderately dirty metal}); \quad (2a) \\
\sigma_{xy} &\propto \sigma_{xx}^{1.6} \quad (\text{dirty metal}). \quad (2b)
\end{align}
Equation (2a) describes the band intrinsic Berry phase contribution to AHE, with the AHE independent of impurity scattering.\textsuperscript{34} Equation (2b) depicts the impurity scattering dominated behavior, where $\sigma_{xy}$ exhibits a power-law scaling relation with $\sigma_{xx}$.\textsuperscript{34,35} The transition occurs at $\sigma_{xx}$ of $\sim 10^3$ S/cm. For thick NCO films, $\sigma_{xx}$ is close to the boundary between these two regions, and both mechanisms can contribute to the measured anomalous Hall signal.

In Fig. 4(a), we fitted the $\sigma_{xy}$ vs. $\sigma_{xx}$ for the ultrathin NCO films by considering both contributions:

$$\sigma_{xy} = A_1 \sigma_{xx}^{1.6} + \sigma_{xy}^{(0)}. \tag{3}$$

Here $A_1$ is the fitting parameter and $\sigma_{xy}^{(0)}$ is the Berry phase contribution.\textsuperscript{34-37} The band intrinsic nature of the latter has been confirmed in thick films from the scaling behavior between $\sigma_{xy}$ and magnetization.\textsuperscript{5} For the 3-5 uc films, the scaling behavior between $\sigma_{xy}$ and $\sigma_{xx}$ exhibits a power law behavior in the metallic region above $T_{up}$, which can be well depicted by Eq. (3). The sign of $\sigma_{xy}$ is thus determined by the relative strength of the positive contribution from dirty metal scattering and the negative contribution from band intrinsic Berry phase effect. With reducing film thickness, the conductivity of NCO decreases, moving further away from the boundary to the moderately dirty region. The corresponding $A_1$ increases, consistent with the raising contribution from dirty metal regime scaling behavior [Fig. 4(b)]. The intrinsic contribution $\sigma_{xy}^{(0)}$ is close to $-2$ $\Omega^{-1}$cm$^{-1}$ and only shows a slight increase. Below $T_{up}$, $\sigma_{xy}$ exhibits very weak $T$-dependence. In addition to the band intrinsic effect, spin-orbit interaction in impurity scattering, known as the side jump effect $\sigma_{xy}^{(1)}$, may also lead to the scattering insensitive AHE in this region. Overall, the AHE for films of this thickness range (3-5 uc) is qualitatively similar to that observed in thicker films.\textsuperscript{3}
The 1.5-2 uc NCO films, on the other hand, exhibit distinct $\sigma_{xy}$ vs. $\sigma_{xx}$ scaling relation. The 2 uc film exhibits a transition to insulating behavior as $R_\square$ exceeds $\frac{h}{e^2}$. While the high temperature AHE scaling still follows Eq. (3), there is a sharp increase in $A_1$. Below $T_{up}$, the sample conductivity falls rapidly due to the strong localization effect. The AHE can be well described by the dirty metal scaling relation alone:

$$\sigma_{xy} = A_2\sigma_{xx}^{1.6}. \quad (4)$$

Similarly, the 1.5 uc sample exhibits insulating behavior over the entire temperature range, and the AHE scaling follows Eq. (4). This is qualitatively different from that for thicker films, where $\sigma_{xy}$ is independent of $\sigma_{xx}$ below $T_{up}$. It confirms that the insulating behavior has a distinct origin compared with the weakly localized behavior of the resistance upturn observed in the 3 uc and thicker films. The negligible contribution of the Berry phase term in the 1.5 uc film is also consistent with the fact that $T_{sc}$ approaches $T_C$ in this sample [Fig. 2(c)], with the sign change behavior hard to resolve [Fig. 3(c)]. It is natural to expect that when the scattering rate well exceeds the Fermi energy, the feature associated with the band intrinsic Berry phase effect is smeared by impurity scattering. It further shows that the spin scattering source is likely associated with the surface/interface of the sample, whose contribution becomes dominant in ultrathin films.

Based on this scenario, we summarized the AHE mechanisms observed in the ultrathin NCO films as well as previously studied thick films. Figure 4(c) shows the temperature-film thickness diagram for the electronic and magnetic state of 1.5-30 uc NCO films. For 2 uc and thicker films, the intermediate temperature region between $T_C$ and $T_{up}$ corresponds to a metallic phase, and the AHE depends on the collective contributions of band intrinsic effect and impurity scattering. Below $T_{up}$, $R_{AHE}$ becomes independent of scattering, which can be due to the band intrinsic or side
jump effect. In the strongly localized regime, the Berry phase effect vanishes, and $R_{AHE}$ is dominated by the dirty metal scaling behavior. The onset of the strongly localized regime is corroborated by $R_e$ exceeding the quantum limit of $\frac{h}{e^2}$\textsuperscript{19,38} The rich electronic/AHE diagram is thus a clear manifestation of the complex energy landscape in NCO associated with magnetic exchange, electron correlation, spin-orbit interaction, and impurity scattering. The film thickness offers an effective control parameter to tune the relative strength between these energy scales, which can be utilized to design application-specific magnetic properties, including the magnetic transition temperature, coercive field, and the strength and sign of anomalous Hall effect.

In summary, we report the intriguing magnetotransport properties of high quality (001) NCO films on MgAl$2$O$_4$ towards the ultrathin thickness limit. NCO films as thin as 1.5 uc (1.2 nm) can sustain strong perpendicular magnetic anisotropy, competitive $T_c$ of 170 K, and robust anomalous Hall effect. The scaling behavior between $\sigma_{xy}$ and $\sigma_{xx}$ reveals the complex interplay between band intrinsic Berry phase effect and impurity scattering, while the film thickness can be leveraged to tune their relative strength. Our study also paves the path for scalable development of NCO based epitaxial magnetic tunnel junctions and sensor devices.

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Reference:


Figure 1 (a) Structure schematic of NCO. (b) XRD $\theta$-$2\theta$ scan of a 60 uc NCO film on MAO with a fit to Laue oscillations near the (004) peak (dotted line). (c) HAADF-STEM and (inset) SAED images taken on a 17 uc film. (d) AFM topography image of a 5 uc NCO film. (e) $R_{\square}(T)$ for 1.5-5 uc NCO.
Figure 2 (a) $\rho_{xy}$ vs $H$ hystereses at 100 K for 1.5-5 uc NCO films. (b-c) Film thickness dependence of (b) $H_C$ at 100 K, and (c) $T_C$, $T_{up}$, and $T_{sc}$. (d) $T_C$ vs. thickness for NCO, magnetic oxide thin films (squares) SRO, and LSMO, and 2D vdW magnets (circles) VSe$_2$, MnSe$_2$, CrSe$_2$, CrI$_3$, CrCl$_3$, FGT, and CGT. Solid symbols: PMA. Open symbols: in-plane magnetic anisotropy.
**Figure 3** (a) AHE taken on 2 uc NCO at various temperatures. Magnetic field range: -10 – 10 kOe for 5 K and 10 K and from -4 – 4 kOe for higher temperatures. (b) AHE taken on 5 uc NCO at various temperatures. (c) $R_{\text{AHE}}$ vs. $T$ for 1.5-5 uc NCO. (d) $n$ and (e) $H_c$ vs. $T$ for 2 uc NCO. (f) $R_{xy}$ as functions of $T$ and $H$ for 2 uc NCO in sweeping down magnetic field.
Figure 4. (a) $\sigma_{xy}$ vs. $\sigma_{xx}$ for 1.5-5 uc NCO films with fits to Eq. (3) and (4) (dash lines). (b) Film thickness dependence of $A_1$, $A_2$ and $\sigma_{xy}^{(0)}$. (c) Temperature-thickness diagram of the AHE scaling behavior. M: metallic. WL: weakly localized. SL: strongly localized. The data for 10-30 uc films are taken from Ref. [3].